

$$\frac{\mu_n C_{ox} W}{2} (V_{GS} - V_T)^2$$

NMOS

$$V_{GS} = V_{DD} - \frac{R_2}{R_1 + R_2} V_{DD}$$

$$V_{SD} = V_{DD} - I_{D0} \cdot R_D$$

PMOS

$$V_{GS} = V_{DD} - \frac{R_2}{R_1 + R_2} V_{DD}$$

$$V_{SD} = V_{DD} - I_{D0} \cdot R_D$$

Converting nMOS circuits to pMOS

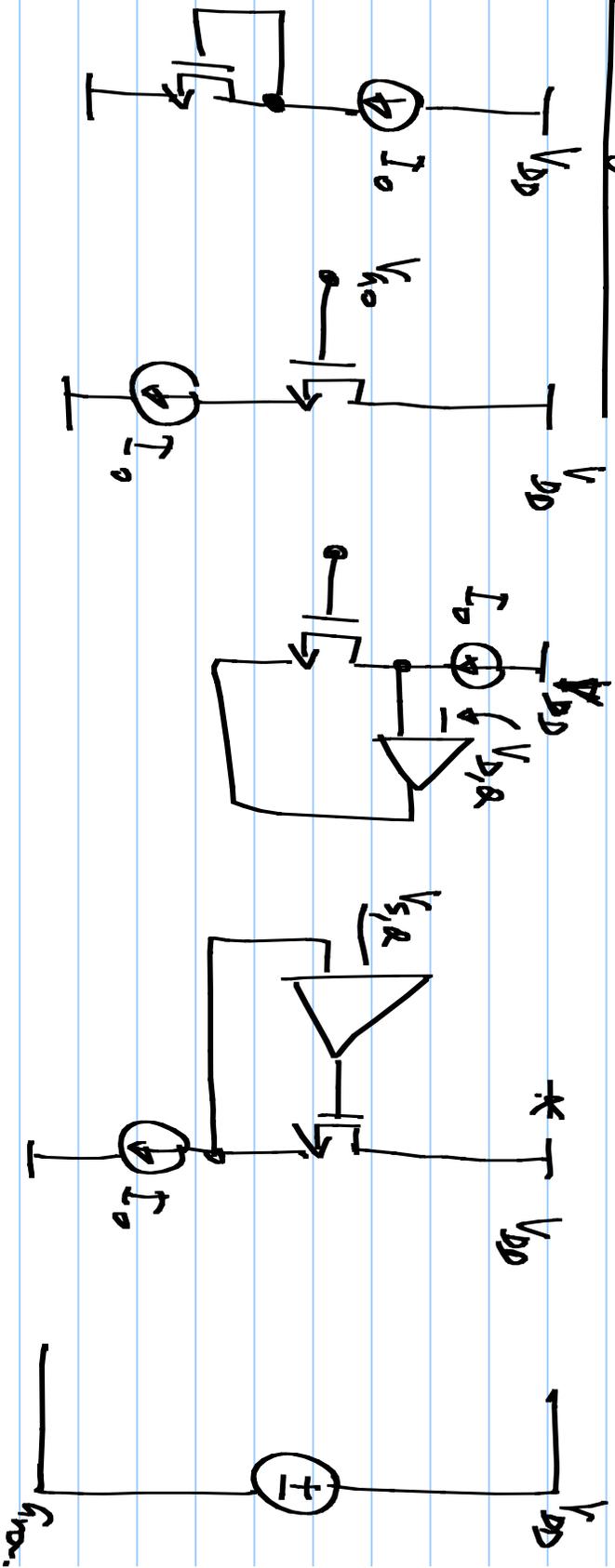
swing limits reversed

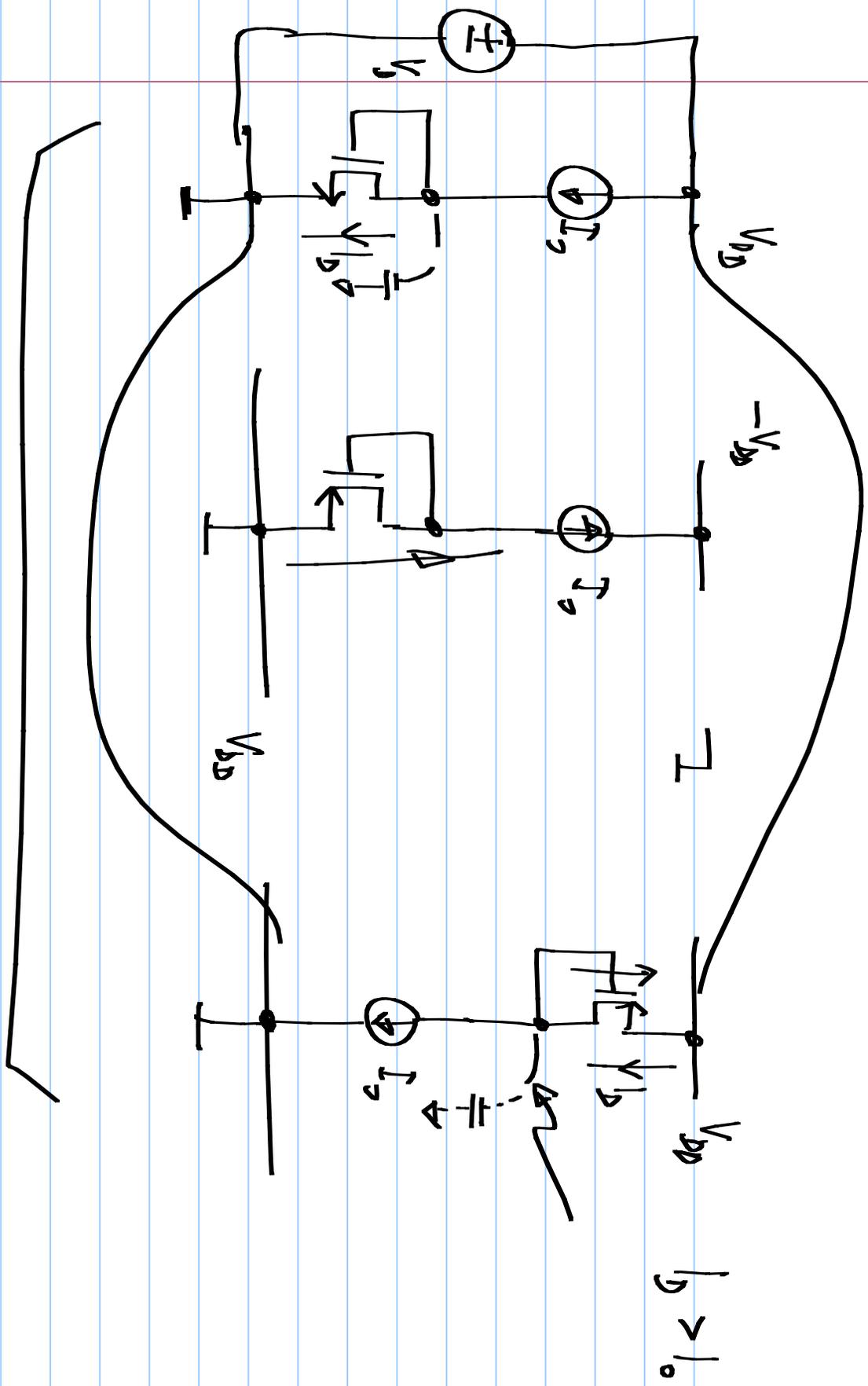
- * substitute nMOS with pMOS
- * Invert the polarity of all biasing sources (V_{DD} , I_b etc.)

Running pMOS & nMOS circuits from common supply rails

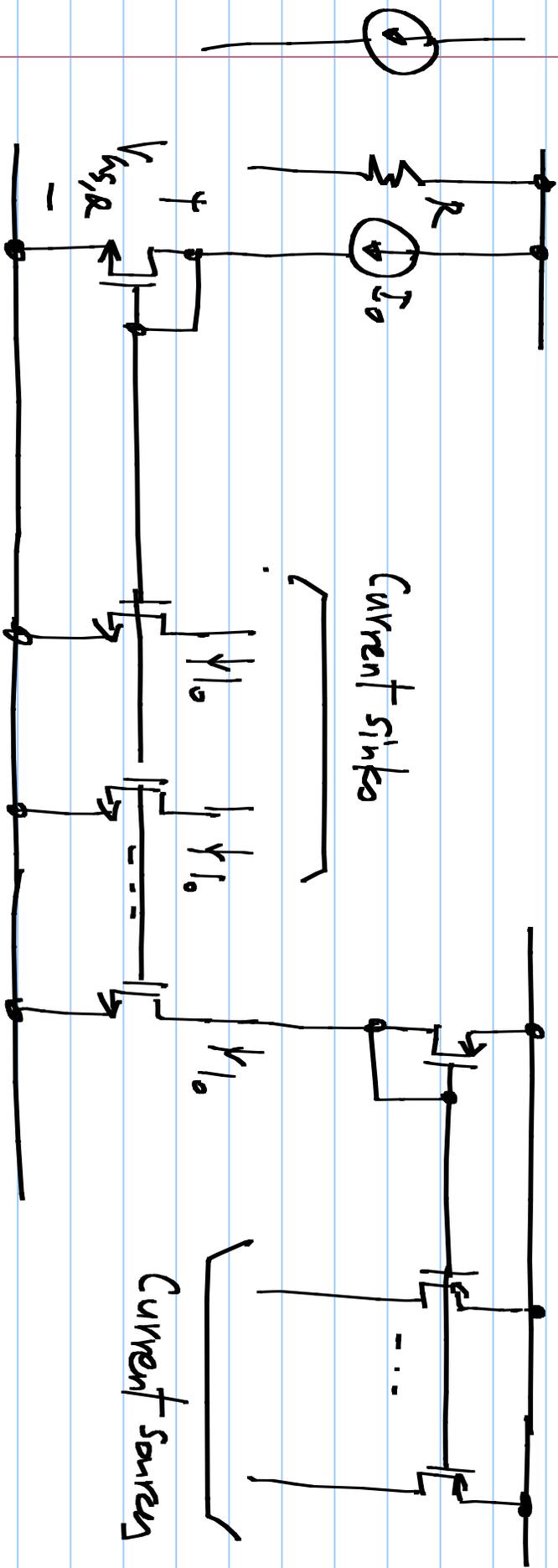
- * ~~From~~ Consider the lowest voltage (-ve terminal of V_{DD}) as ground
- * Refer signal source & load to this ground

Biasing arrangements

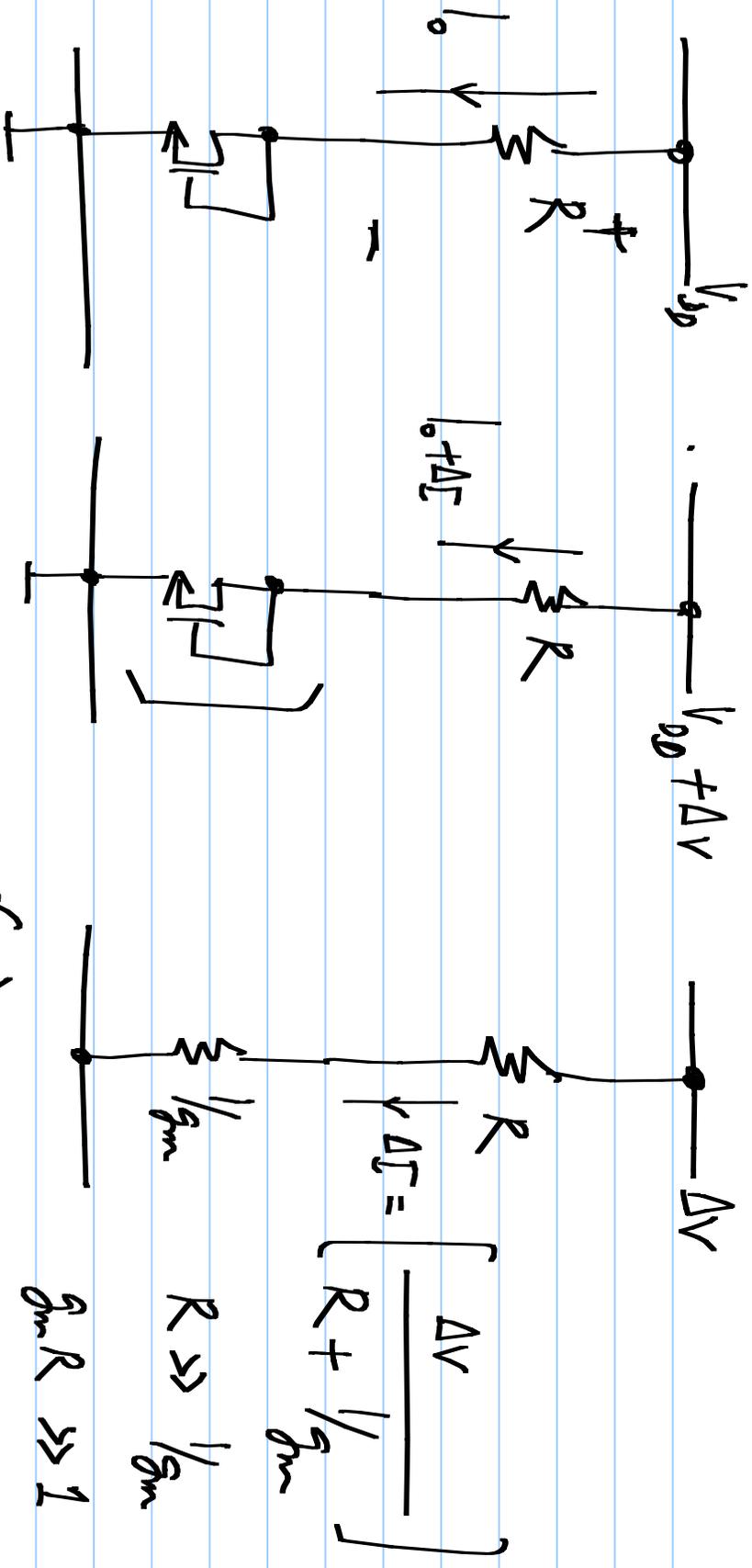




$$R = \frac{V_{DD} - V_{GS/R}}{I_0}$$

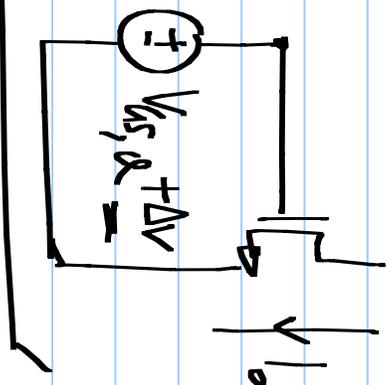


$V_T : 0$ $V_{GS/R}$ $V_{GS/R}$



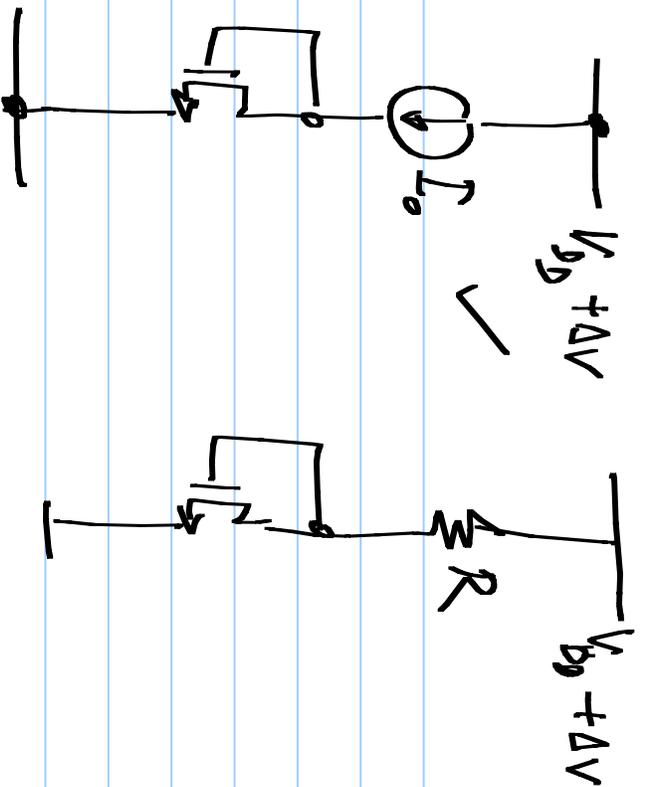
$$g_m = \frac{2I_0}{V_{GS} - V_T}$$

$$\frac{2(I_0 R)}{(V_{GS} - V_T)} \gg 1$$



$\Delta V \approx g_m$

$\rightarrow \Delta V \cdot g_m$



$\Delta V = \frac{g_m}{1 + g_m R}$

$\rightarrow \Delta V \cdot \frac{g_m}{1 + g_m R}$